Dual 2-input OR gate Rev. 4 — 27 September 2013

Product data sheet

1. General description

The 74HC2G32; 74HCT2G32 is a dual 2-input OR gate. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

2. Features and benefits

- Wide supply voltage range from 2.0 V to 6.0 V
- Input levels:
 - ◆ For 74HC2G32: CMOS level
 - For 74HCT2G32: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1.Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
74HC2G32DP	–40 °C to +125 °C	TSSOP8	SOT505-2							
74HCT2G32DP										
74HC2G32DC	–40 °C to +125 °C	VSSOP8 plastic very thin shrink small outline package; 8 leads;		SOT765-1						
74HCT2G32DC			body width 2.3 mm							
74HC2G32GD	–40 °C to +125 °C	XSON8	SON8 plastic extremely thin small outline package; no leads;							
74HCT2G32GD			8 terminals; body $3 \times 2 \times 0.5$ mm							



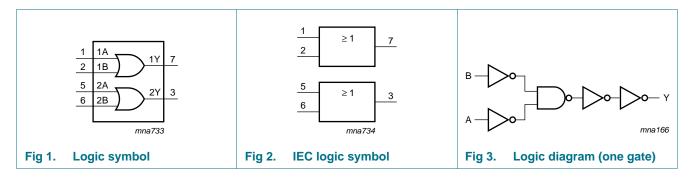
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4. Marking

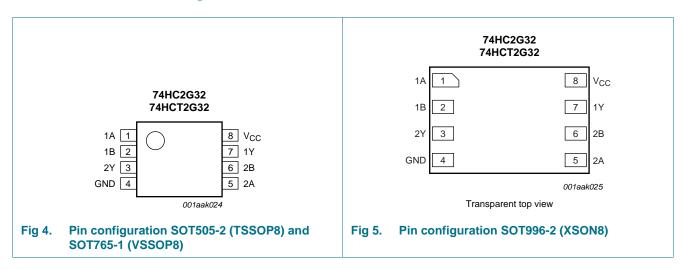
Table 2. Marking code	
Type number	Marking code ^[1]
74HC2G32DP	H32
74HCT2G32DP	T32
74HC2G32DC	H32
74HCT2G32DC	T32
74HC2G32GD	H32
74HCT2G32GD	T32

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information



6.1 Pinning

6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4.Function table^[1]

Input	Output	
nA	nB	nY
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V_{l} < -0.5 V or V_{l} > V_{CC} + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	V_O < –0.5 V or V_O > V_{CC} + 0.5 V	<u>[1]</u> _	±20	mA
lo	output current	$V_{O} = -0.5 \text{ V}$ to ($V_{CC} + 0.5 \text{ V}$)	<u>[1]</u> -	25	mA
I _{CC}	supply current		<u>[1]</u> _	50	mA
I _{GND}	ground current		<u>[1]</u> –50	-	mA
T _{stg}	storage temperature		-65	+150	°C
PD	dynamic power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8 package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	7	74HC2G32			74HCT2G32		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7.Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C 1	to +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC2G	32									
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
011	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_0 = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.18	4.32	-	4.13	-	3.7	-	V
		$I_0 = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.68	5.81	-	5.63	-	5.2	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_0 = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		$I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC} \text{ or GND};$ $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{CC}	supply current		-	-	1.0	-	10	-	20	μΑ

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Symbol	Parameter	Conditions		25 °C		_40 °C	to +85 °C	–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
Cı	input capacitance		-	1.5	-	-	-	-	-	pF
74HCT2	G32									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH} HIGH-level		$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4.0 mA	4.18	4.32	-	4.13	-	3.7	-	V
V _{OL}	OL LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		l _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	1.0	-	10	-	20	μA
Δl _{CC}	additional supply current	per input; $V_{CC} = 4.5 V \text{ to } 5.5 V;$ $V_I = V_{CC} - 2.1 V; I_O = 0 A$	-	-	300	-	375	-	410	μA
CI	input capacitance		-	1.5	-	-	-	-	-	pF

Table 7.Static characteristics ... continuedVoltages are referenced to GND (ground = 0 V).

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions			25 °C		–40 °C t	o +85 °C	–40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HC2G	32						·				
t _{pd}	propagation	nA, nB to nY; see Figure 6	[1]								
delay	$V_{CC} = 2.0 V$		-	24	75	-	95	-	110	ns	
		$V_{CC} = 4.5 V$		-	9.0	15	-	19	-	22	ns
		$V_{CC} = 6.0 V$		-	7.0	13	-	16	-	20	ns
tt	transition	nY; see <u>Figure 6</u>	[2]								
	time	$V_{CC} = 2.0 V$		-	18	75	-	95	-	125	ns
		$V_{CC} = 4.5 V$		-	6	15	-	19	-	25	ns
		$V_{CC} = 6.0 V$			5	13	-	16	-	20	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[3]</u>	-	10	-	-	-	-	-	pF

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Symbol	Parameter	Conditions		25 °C		–40 °C to +85 °C		–40 °C t	o +125 °C	Unit	
				Min	Тур	Max	Min	Max	Min	Max	
74HCT2	G32	'									
t _{pd} propagation delay	nA, nB to nY; see Figure 6	[1]									
	delay	$V_{CC} = 4.5 V$		-	13	24	-	30	-	36	ns
tt	transition	nY; see <u>Figure 6</u>	[2]								
	time	$V_{CC} = 4.5 V$		-	6	15	-	19	-	22	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[3]</u>	-	11	-	-	-	-	-	pF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

$\label{eq:ttime_time} [2] \quad t_t \text{ is the same as } t_{TLH} \text{ and } t_{THL}.$

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 P_{D} = $C_{PD} \times V_{CC}{}^{2} \times f_{i} \times N$ + $\Sigma(C_{L} \times V_{CC}{}^{2} \times f_{o})$ where:

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

12. Waveforms

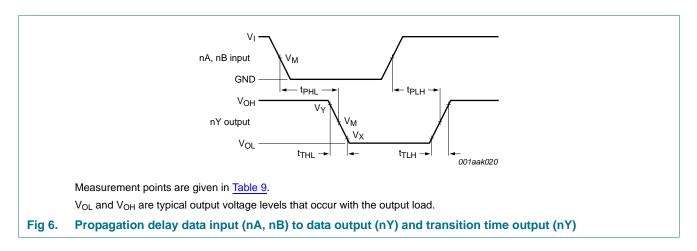


Table 9. Measurement points									
Туре	Input	Output							
	V _M	V _M	V _X	V _Y					
74HC2G32	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}					
74HCT2G32	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}					

74HC_HCT2G32 Product data sheet

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74HC2G32; 74HCT2G32

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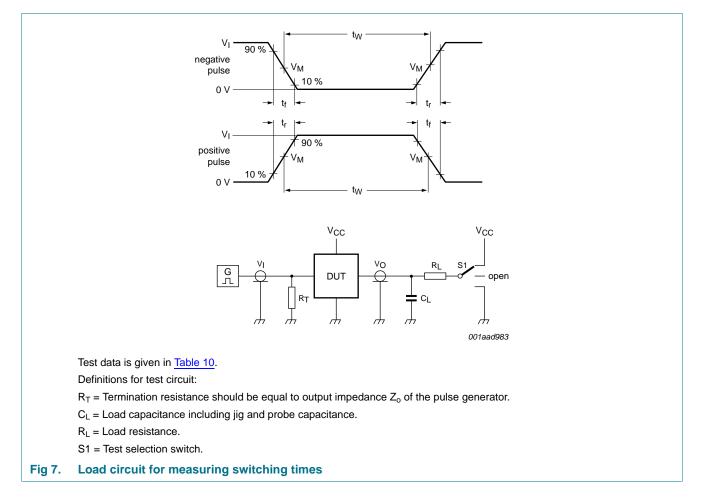
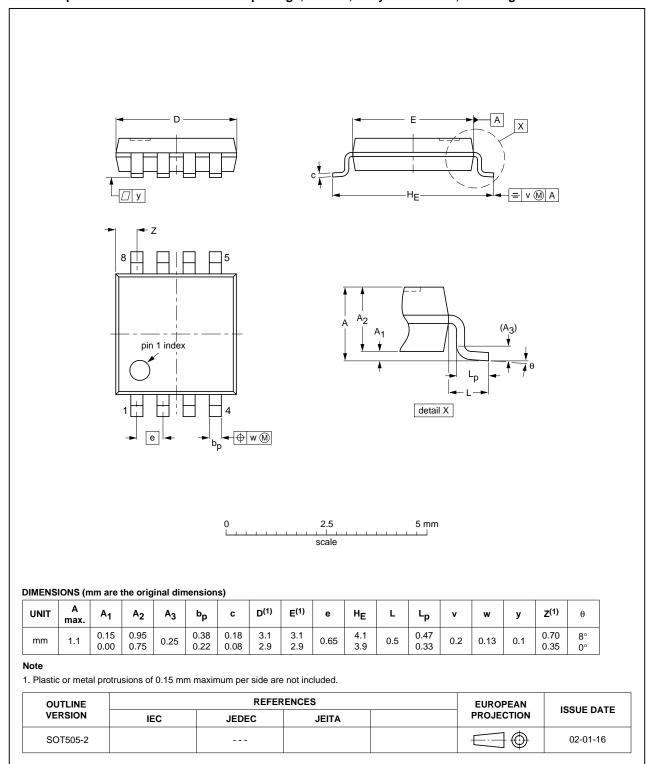


Table 10. Test data

Туре	Input		Load		S1 position
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}
74HC2G32	GND to V_{CC}	≤ 6 ns	50 pF	1 kΩ	open
74HCT2G32	GND to 3 V	≤ 6 ns	50 pF	1 kΩ	open

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13. Package outline



TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

Fig 8. Package outline SOT505-2 (TSSOP8)

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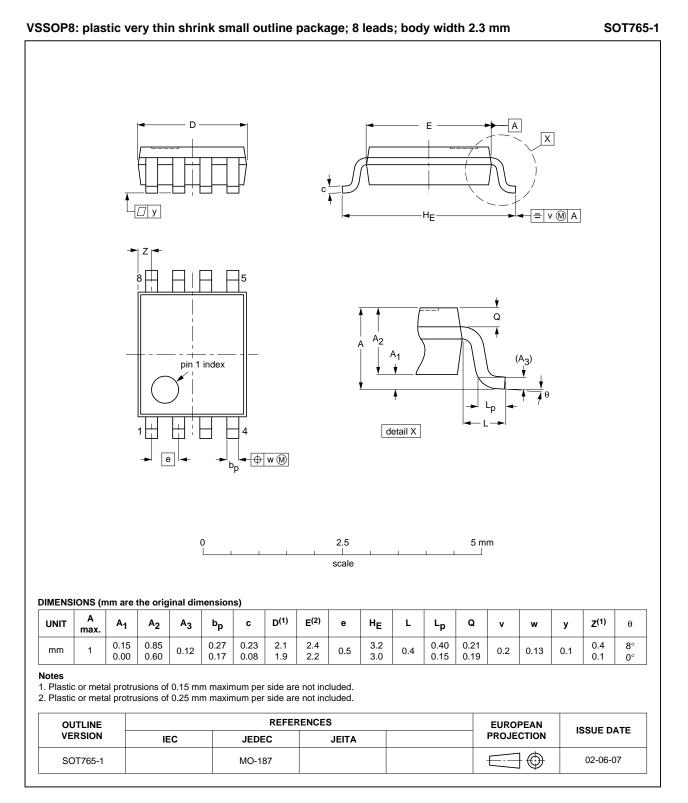
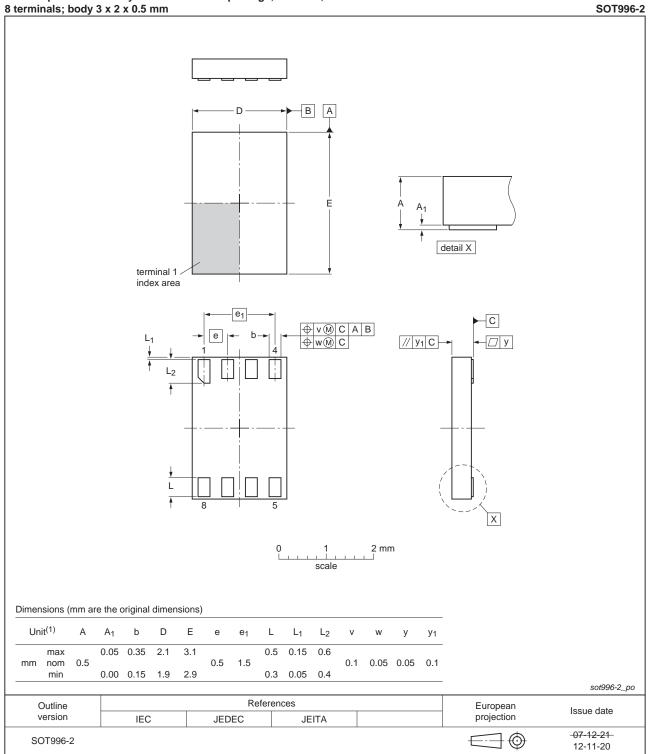


Fig 9. Package outline SOT765-1 (VSSOP8)

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XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 3 x 2 x 0.5 mm

Fig 10. Package outline SOT996-2 (XSON8)

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14. Abbreviations

Table 11. Abbreviations				
Acronym	Description			
CMOS	Complementary Metal Oxide Semiconductor			
DUT	Device Under Test			
ESD	ElectroStatic Discharge			
HBM	Human Body Model			
MM	Machine Model			
TTL	Transistor-Transistor Logic			

15. Revision history

Table 12. Revision I	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G32 v.4	20130927	Product data sheet	-	74HC_HCT2G32 v.3
Modifications:	 For type nun 	nbers 74HC2G32GD and 74HC	T2G32GD XSON8U	has changed to XSON8.
74HC_HCT2G32 v.3	20090512	Product data sheet	-	74HC_HCT2G32 v.2
74HC_HCT2G32 v.2	20031030	Product specification	-	74HC_HCT2G32 v.1
74HC_HCT2G32 v.1	20020717	Product specification	-	-

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Document status[1][2]	Product status ^[3]	Definition
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Date of release: 27 September 2013 Document identifier: 74HC_HCT2G32